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Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126821		APPLICATION NO. 10/565,968		
	INFORMATION DISCLOSURE STATEMENT						1	
	(Use several sheets if necessary)			APPLICANT(S) Satoshi TAKEI et al.				
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Examiner Initials	Cite No.	Document Number	Da	te	Country		With English Abstract	With English Translation
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W	2.	JP-A-2002-47430	02-2002		Japan		х	х
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Sp.	4.	WO 02/05035	01-2002		WIPO		Χ.	· <del>.</del>
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